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Supporting Information

Low-temperature facile solution-processed gate dielectric and active channel for oxide thin film transistors

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The performances of TFTs transfer were demonstrated in figure S1.

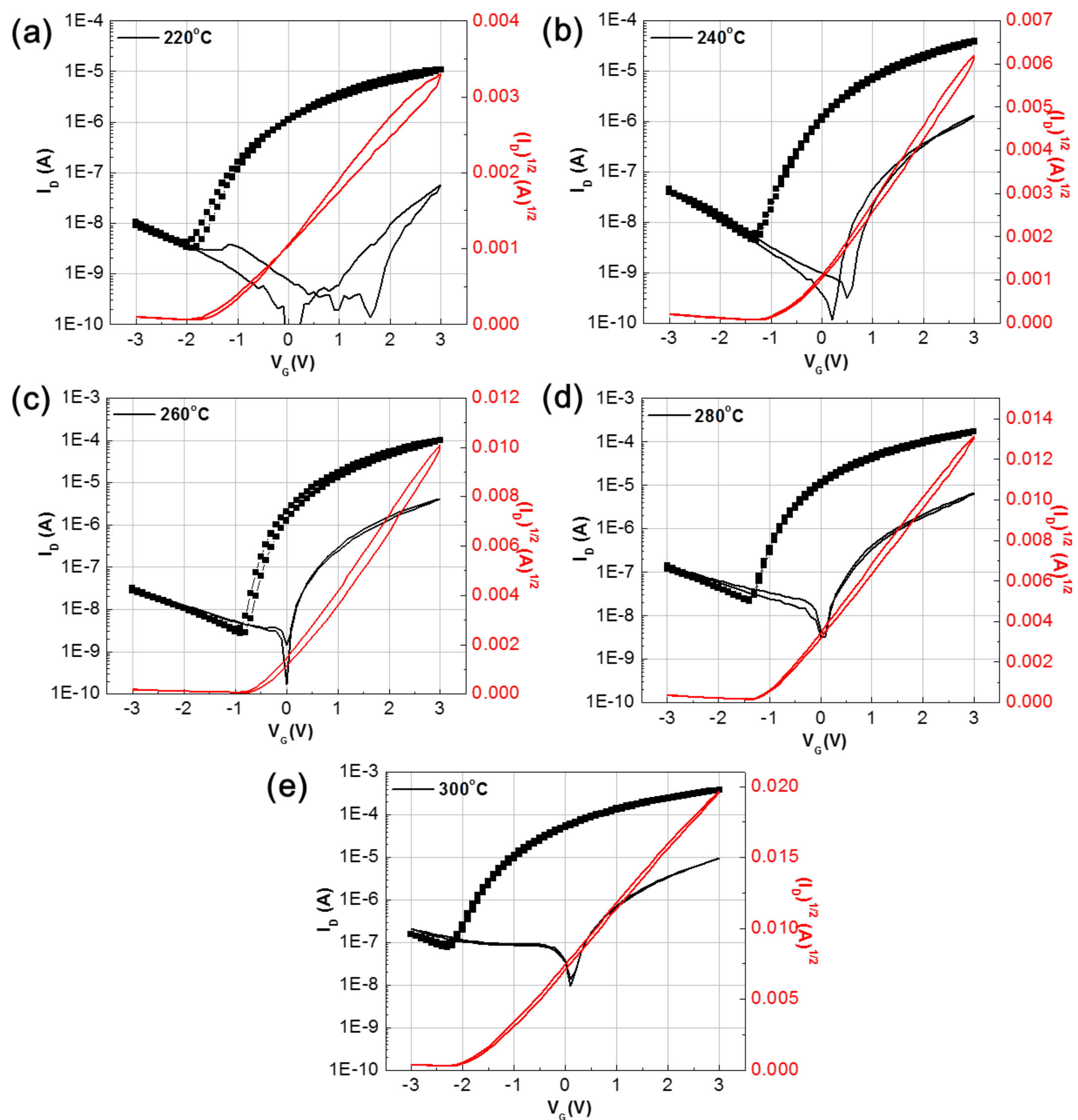

Figure S1 Transfer performances of the samples. The annealing temperatures of them are (a) 220 ℃, (b) 240 ℃, (c) 260 ℃, (d) 280 ℃ and (e) 300 ℃.